Express Mail No.: <u>EV 371 773 148 US</u>

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

pplication of: Wai Mun Lee

Confirmation No.:

9136

Serial No.:

10/630,300

Art Unit:

1751

Filed:

July 30, 2003

Examiner:

To be assigned

For:

Cleaning Compositions and Methods of

Attorney Docket No.: 60937-194-US

Use Thereof

(formerly 8317-194-999)

## TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS POWERS OF RECORD

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above identified patent application.

<u>Please change the attorney docket number to 60937-194-US</u>. Future correspondence should be forwarded to James S. McDonald, customer no. 24341.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310 (Order No. 60937-194-US). A copy of this sheet is enclosed for such purpose.

Respectfully submitted,

Date March 12, 2004

MORGAN, LEWIS & BOCKIUS LLP

3300 Hillview Avenue Palo Alto, CA 94304

(650) 493-4935

## REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

7 tol 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

Vice President, R&D and Engineering

Address:

2520 Barrington Court Hayward, CA 94545

	(°) (°)	·			
	MAR 1 2 2004	Schedule A			
App #	Title	¹lnventor(s):		New Allomey. Dockel No.*	
	Compositions for Cleaning Organic				
-	and Plasma Etched Residues for		.=		
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
	Method of and Apparatus for		00/00/0004	00007 444 110	0247 444 000
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
00/005 070	Chemical Mechanical Polishing	Concil at al	11/06/2001	60937-114-US	8317-114-999
09/985,870	Compositions	Small, et al.	11/00/2001	00937-114-03	0317-114-999
	Oxalic Acid as a Semiaqueous				,
40/404 706	Cleaning Product for Copper and Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/421,706	Sulfoxide Pyrolid(in)one Alkanolamine	Lee, et al.	04/24/2003	00307-110-00	0011-110-000
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
10/193,103	Cleaner Composition	Znou, ot al.	0771272002	00007 110 00	
	Method for the Deposition of Materials				
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
00/070,011	Post Etch Cleaning Composition for				
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
	Photolytic Conversion Process to				
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including		•		
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation			·	
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate		0.4.10.0.10.000	20007 400 110	0047 400 000
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including	<b>-</b> ,			
	Nucleophilic Amine Compound				
40/405 005	Having Reduction and Oxidation	Loo et el	05/01/2002	60937-135-US	8317-135-999
10/135,695	Potential Paraving Same	Lee, et al.  Melvin K. Carter	05/01/2002	60937-133-US	8317-137-999
10/448,127	Fluoride Layer and Removing Same	Meivin K. Carter	05/30/2003	00937-137-03	0317-137-999
	Process for the Use of Bis-Choline				
	and Tris-Choline in the Cleaning of				
40/000 057	Quartz-Coated Polysilicon and Other	Charm et al	.10/22/2003	60937-139-US	8317-139-999
10/689,657	Materials  Classica Compositions Containing	Charm, et al.	.10/22/2003	00301-138-03	0011-105-555
	Cleaning Compositions Containing Hydroxylamine Derivatives and		•		
	Process Using Same for Residue				
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
10/003,020	T CONTOVAL	2.700, 0.01.			

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8317-141-999

8317-142-888

Melvin K. Carter

Lee, et al.

10/22/2003

05/02/2003

60937-141-US

60937-142-PR

Composition for Exfoliation Agent to be Used to Remove Resist Residues

Reducing Oxide Loss When Using Fluoride Chemistries to Remove Post-Etch Residues in Semiconductor

Processing

10/689,616

60/467,131

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	Title 7	la voatorio	Filing Date	New Attorney  Docket No.	Former Attorney  Docket No.
App.#	Constitution of the state of th	i inventor(s)	, Dale	COUNTY OF THE PROPERTY OF THE	DOCKET INC. X
40/000 204	Method for Depositing Patterned Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
10/630,301	Methods for the Deposition of Silver	mill, et al.	01/30/2003	00937-143-03	0017-140-999
	and Silver Oxide Films and Patterned	•			
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
10// 10,030	Semiconductor Process Residue	rtuari, ot al.	11/10/2000	00001 111 00	0011 111 000
10/162,679	Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
10/102,010	System and Method for Cleaning				
	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing				
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
	<u> </u>	•			
	Method of Depositing Nanostructured	1	00/00/0000	00007.450.110	0047 450 000
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
40/000 070	Hydrothermal Treatment of	Mulchariae et al	40/22/2002	60937-167-US	8317-167-999
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002 10/11/2002	60937-167-US	8317-168-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	00937-100-03	0317-100-999
10/401 405	Chemical Mechanical Polishing Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
10/401,405	Aqueous Phosphoric Acid	Oman, et al.	03/21/2003	00307-171-00	0017 171 000
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
10/000,300	Load Lock System for Supercritical	Daviou, or all			
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10. 100,000	Automated Dense Phase Fluid				
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
<del></del>	Residue Removers for				,
	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
	Titanium Carboxylate Films for Use in			_	
10/377,533	Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
	Remover Formulation Containing				
	Fluoride for Use During	112	04/48/0000	60027 405 DD	0247 405 000
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
	Cleaning Composition for Removing				
60/464 405	Resists and Manufacturing Method of	Hiracawa et al	04/21/2003	60937-186-PR	8317-186-888
60/464,125	Semiconductor Devices  Deposition of Permanent Polymer	Hirasawa, et al.	04/21/2003	00331-100-PK	0317-100-000
10/422 212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999
10/422,212	Structures for OLLD Fabrication	i toman, et al.	U-1/2012000	30007 107-00	101-000

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App #	Title			New/Attorney Docket No.	Former Attorney Docket No.
. Арра <del>ты</del>	Seimconductor Process Residue		**************************************	P. D. CONOTTATO	
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,030	Cleaning Compositions and Method of	Wal Mail 200			
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
10/030,300	Compositions and Methods for	Trai man 200	01/00/2000		
•	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
00/310,337	CMP Method for Copper, Tungsten,	Oriono, or all	1111012000	00001 200 111	
	Titanium, Polysilicon, and Other				Ì
	Substrates Using Organosulfonic		•		
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
10/090,023	PeriodicAcid Compositions for	· ·			
	Polishing Nobel Metal/High K				
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
00/434,334	Cerium Oxide Abrasives for Chemical	1 tobolt o. ollian			
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
00/000,020	iniocriainica. i ciiciini g	•			
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
00/010,700	Periodic Acid Compositions for	, , , , , , , , , , , , , , , , , , , ,		,	
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
00/10/1,000	Chemical Mechanical Polishing				
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
10,000,100	Alumia Abrasive for Chemical	· · · · · · · · · · · · · · · · · · ·			
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
00/01/1,020					
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				•
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
	Mechanical Planarization of Tantalum		<u>.</u>		
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
	Alumina Abrasive for Chemical				
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
	Particulate or Particle-Bound	-			<u>.</u>
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound				
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water				0047 000
60/533,054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
1	Removal of Post Etch Residues and				
	Copper Contamination From Low-K				'
	Dielectrics Using Superciritcal CO2		40/44/0000	00007 005 55	0247 005 000
60/511,949		Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
	Method and Apparatus for Substrate		40/00/0000	60027 000 110	8317-226-999
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	0311-220-858

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60/515,450	Method of Chemically Mechanically Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888